



DSS8110Y

100V LOW V_{CE(sat)} NPN SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Complementary PNP Type Available (DSS9110Y)
- Ultra Small Surface Mount Package
- "Lead Free", RoHS Compliant (Note 1)
- Halogen and Antimony Free, "Green Device" (Note 2)

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)

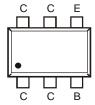








Device Symbol



Pin-Out Top

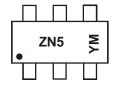
Ordering Information (Note 3)

ſ	Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	DSS8110Y-7	ZN5	7	8mm	3,000

Notes:

- 1. No purposefully added lead.
- 2. Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

Marking Information



ZN5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: X = 2010) M = Month (ex: 9 = September)

Date Code Key

Year	20	10	20	11	20	12	20	13	20	14	20	15
Code	>	(`	1	Ž	7	A	4	[3	()
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings @TA = 25°C unless otherwise specified

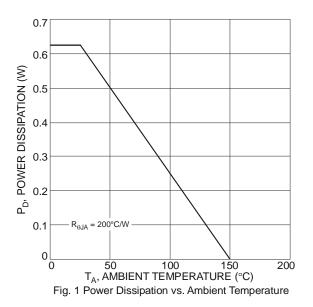
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current - Continuous	Ic	1	Α
Peak Pulse Collector Current	I _{CM}	3	Α
Base Current – Continuous	I _B	0.3	А

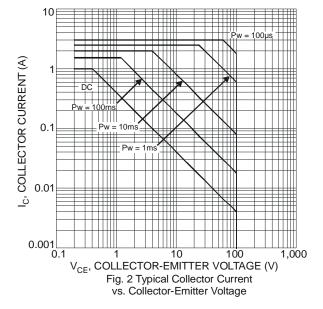
Thermal Characteristics

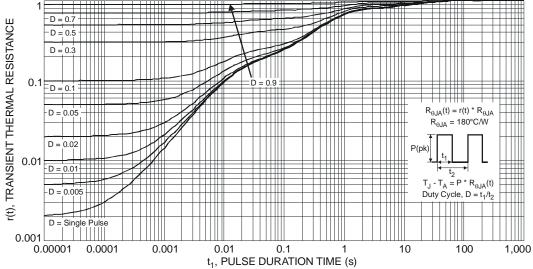
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ T _A = 25°C	P _D	625	mW
Thermal Resistance, Junction to Ambient (Note 4) @ T _A = 25°C	$R_{ hetaJA}$	200	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

4. Device mounted on FR-4 PCB, with minimum recommended pad layout.





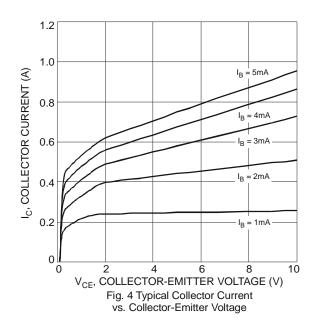


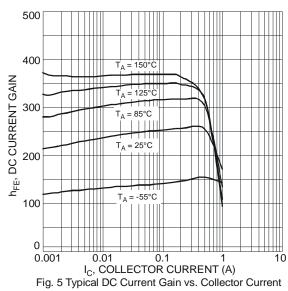


Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Collector-Base Breakdown Voltage	BV _{CBO}	120	_	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	100	_	_	V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	5			V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_	_	100	nA	$V_{CB} = 80V, I_{E} = 0$
Concetor Gaton Current	iCBO	_	_	50	μΑ	$V_{CB} = 80V, I_{E} = 0, T_{A} = 150^{\circ}C$
Collector Cutoff Current	I _{CES}	_		100	nA	$V_{CE} = 80V, V_{BE} = 0$
Emitter Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 4V, I_{C} = 0$
ON CHARACTERISTICS (Note 5)						
		150	_	_		$V_{CE} = 10V$, $I_C = 1mA$
DC Current Gain	h _{FF}	150	_	500	V	$V_{CE} = 10V, I_{C} = 250mA$
Do ouncir cam	''FE	100	_	_		$V_{CE} = 10V, I_{C} = 500mA$
		80	_	_		$V_{CE} = 10V, I_{C} = 1A$
		_	_	40		$I_C = 100 \text{mA}, I_B = 10 \text{mA}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	_	120	mV	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
		_	_	200		$I_C = 1A$, $I_B = 100mA$
Collector-Emitter Saturation Resistance	R _{CE(sat)}	_		200	mΩ	$I_C = 1A$, $I_B = 100mA$
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	_	1.05	V	$I_C = 1A$, $I_B = 100mA$
Base-Emitter Turn On Voltage	V _{BE(on)}	_	_	0.9	V	$V_{CE} = 10V, I_{C} = 1A$
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	_	_	7.5	pF	V _{CB} = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f⊤	100	_	_	MHz	V _{CE} = 10V, I _C = 50mA, f = 100MHz

Notes: 5. Measured under pulsed conditions. Pulse width = $300\mu s$. Duty cycle $\leq 2\%$.







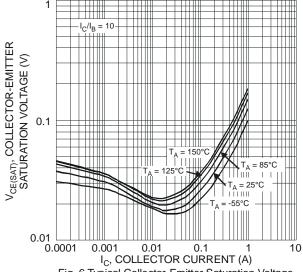


Fig. 6 Typical Collector-Emitter Saturation Voltage vs. Collector Current

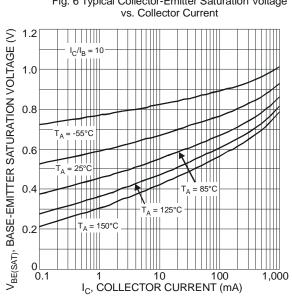
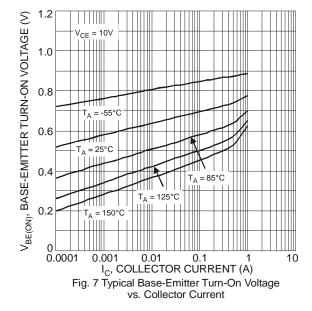
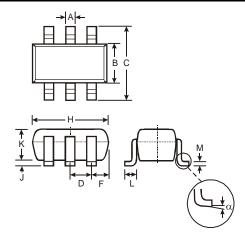


Fig. 8 Typical Base-Emitter Saturation Voltage vs. Collector Current



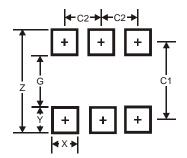
Package Outline Dimensions



SOT-363						
Dim	Min Max					
Α	0.10	0.30				
В	1.15	1.35				
С	2.00	2.20				
D	0.65	Тур				
F	0.40	0.45				
Ι	1.80	2.20				
J	0	0.10				
K	0.90 1.00					
L	0.25 0.40					
М	0.10	0.22				
α 0° 8°						
All Dimensions in mm						



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2010, Diodes Incorporated

www.diodes.com